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ALTERNATIVE TO PTO/SB/08a/b (06-03)

Substitute for form 1449/PTO				Complete if Known		
				Application Number	To be assigned 15378	
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s	STATEMENT BY APPLICANT			First Named Inventor	Robert DWILINSKI	
_				Art Unit	Net-yet-assigned- 1792	
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Sheet	1	of	1	Attomey Docket Number	204552035400	

			U.S. PA	TENT DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number Number-Kind Coda <sup>2</sup> (#known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	2.	JP-10-7496	1-13-1998		abstract	
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EXAMINER: initial is information considered, whether or not classion is in conformance with MPEP 609. Draw line through classion if not in conformance and not considered, include copy of this form with next communication to applicant. "Applicants unique actions designation number (options)." See Rivids Codes of UNIPPO Plante (Document of the UNIPPO Plante) Commented is traversization of MPEP 610 At "Their formities date used with decorations by the option of the UNIPPO Plante (Document of the UNIPPO Plante) Comment of the UNIPPO Plante (Document of UNIPPO Plante) Plante

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-lesue number(s), publisher, city and/or country where published.	T²		
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\*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English languaga Translation is attached.